

U.S. Patent Application Serial No. 09/456,531  
Amendment dated February 19, 2004  
Reply to OA of November 19, 2003

**IN THE CLAIMS**

Please amend claims 1, 15, 21 and 22 as follows:

**Claim 1 (Currently Amended):** An electrode structure including a bonding pad formed on an insulation film without penetrating the insulation film, the insulation film being formed above a base structure,

the insulation film comprising a plurality of poles of polyimide, a first film formed on each side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on the side surface thereof,

wherein said plurality of poles are surrounded with the first film respectively.

**Claim 2 (Canceled).**

**Claim 3 (Previously Presented):** A semiconductor light-emitting device having a waveguide including an active layer or a light absorption layer, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide,

the upper electrode having an electrode structure,

the electrode structure including a bonding pad formed on an insulation film without penetrating the insulation film, the insulation film being formed above a base substrate,

the insulation film comprising a plurality of poles of polyimide, a first film formed on each

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side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on side surfaces thereof.

**Claim 4 (Original):** A semiconductor light-emitting device according to claim 3, wherein the first film is also formed on upper surfaces of the poles.

**Claim 5 (Canceled).**

**Claim 6 (Previously Presented):** A semiconductor light-emitting device according to claim 3, wherein

the first film is also formed on upper surfaces of the second film.

**Claim 7 (Previously Presented):** A semiconductor light-emitting device according to claim 3, wherein

a third film of an insulation material is sandwiched between the insulation film and the bonding pad.

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**Claims 8-10 (Canceled).**

**Claim 11 (Previously Presented):** A semiconductor light-emitting device according to claim 3, wherein

the insulation film is formed on a layer formed on the base substrate, the layer being formed of a material having a higher hardness than the polyamide.

**Claims 12-14 (Canceled).**

**Claim 15 (Currently Amended):** A semiconductor light-emitting device according to claim 13 3, further comprising

a high resistance layer formed on a side of the waveguide; and  
said electrode structure formed on the high resistance layer.

**Claims 16-18 (Canceled).**

**Claim 19 (Previously Presented):** An electrode structure according to claim 1, wherein the first film is also formed on upper surfaces of the second film.

**Claim 20 (Previously Presented):** A semiconductor light-emitting device according to claim 1, wherein the first film is also formed on upper surfaces of the second film.

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**Claim 21 (Currently Amended):** A semiconductor light-emitting device according to claim 13 3, wherein

the first film is also formed on upper surfaces of the poles.

**Claim 22 (Currently Amended):** A semiconductor light-emitting device according to claim 13 3, wherein

the first film is also formed on upper surfaces of the second film.